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(71) Applicant: **APPLIED MATERIALS, INC.** [US/US];
3080 Bowers Avenue, Santa Clara, California 95054 (US).

(72) Inventors: **CONG, Zhepeng**; c/o Applied Materials, Inc.,
Law Dept., M/S 1269, 3050 Bowers Avenue, Santa Clara,

California 95054 (US). **SMITH, Nimrod**; c/o Applied Materials, Inc., Law Dept., M/S 1269, 3050 Bowers Avenue, Santa Clara, California 95054 (US). **MORADIAN, Ala**; c/o Applied Materials, Inc., Law Dept., M/S 1269, 3050 Bowers Avenue, Santa Clara, California 95054 (US).

(74) Agent: **PATTERSON, B. Todd** et al.; Patterson + Sheridan LLP, 24 Greenway Plaza, Suite 1600, Houston, Texas 77046 (US).

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(54) Title: EPI ISOLATION PLATE WITH GAP AND ANGLE ADJUSTMENT FOR PROCESS TUNING

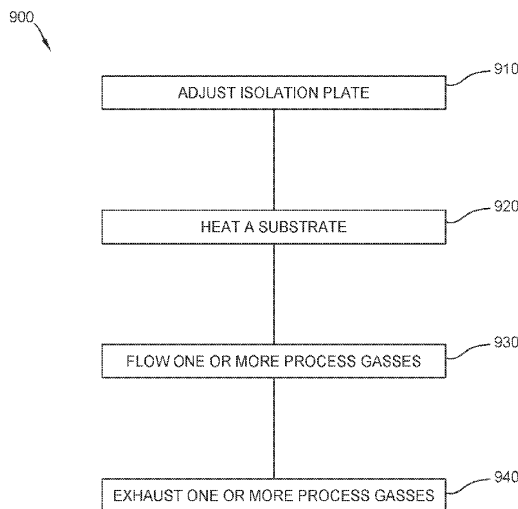


FIG. 9

(57) Abstract: The present disclosure relates to methods and devices for processing substrates, suitable for use in semiconductor manufacturing. The method includes heating a substrate positioned on a substrate support. The method includes moving an isolation plate adjust one or more of: a height of the isolation plate, or an angle of the isolation plate such that the isolation plate moves to a non-parallel orientation relative to the substrate. The method includes flowing one or more process gases over the substrate to deposit a material on the substrate, the flowing of the one or more process gases over the substrate including guiding the one or more process gases through one or more flow paths defined at least in part by a space between the isolation plate and the substrate.

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